April 1999

FDN361AN

FAIRCHILD

SEMICONDUCTOR TM

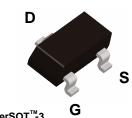
FDN361AN N-Channel, Logic Level, PowerTrench[™]

General Description

This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

Applications

- DC/DC converter
- Load switch
- Motor drives

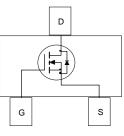


Features

• 1.8 A, 30 V.
$$R_{DS(on)} = 0.100 \text{ W} @ V_{GS} = 10 \text{ V}$$

 $R_{DS(on)} = 0.150 \text{ W} @ V_{GS} = 4.5 \text{ V}.$

- Low gate charge (2.1nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R_{DS(on)}.
- High power version of industry standard SOT-23 package. Identical pin out to SOT-23 with 30% higher power handling capability.



SuperSOT[™]-3

Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		FDN361AN	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage - Continuous		<u>+</u> 20	V
ID	Drain Current - Continuous	(Note 1a)	1.8	А
	- Pulsed		8	
PD	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
TJ, Tsta	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R _θ JC	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
361	FDN361AN 7"		8mm	3000 units	

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	30			V
BVoss ATJ	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25°C		24		mV/∘C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)		-1	1		
V _{GS(th)}	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, \ I_{\text{D}} = 250 \ \mu\text{A}$	1	1.8	3	V
<u>A</u> VGS(th) ∆TJ	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu A$, Referenced to 25°C		-4.2		mV/∘C
R _{DS(on)}	Static Drain-Source On-Resistance			0.072 0.107 0.105	0.1 0.16 0.15	Ω
D(on)	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	8			Α
GFS	Forward Transconductance	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1.8 \text{ A}$		5		S
Dynami	c Characteristics					
liss	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$		220		pF
Soss	Output Capacitance			50		pF
rss	Reverse Transfer Capacitance			20		pF
Switchir	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 V, I_D = 1 A,$		3	6	ns
t	Turn-On Rise Time	V_{GS} = 10 V, R_{GEN} = 6.0 Ω		11	22	ns
t _{d(off)}	Turn-Off Delay Time			7	14	ns
t _f	Turn-Off Fall Time			3	6	ns
Qg	Total Gate Charge	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 1.8 \text{ A},$		2.1	4	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$		0.8		nC
Q _{gd}	Gate-Drain Charge			0.7		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings	-	1	1	•
	Mariana Cantinuan Daria Carr	Diada Forward Current			0.42	А
ls	Maximum Continuous Drain-Source				0.42	<i>/</i> `

R_{gJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{gJC} is guaranteed by design while R_{gJA} is determined by the user's board design.

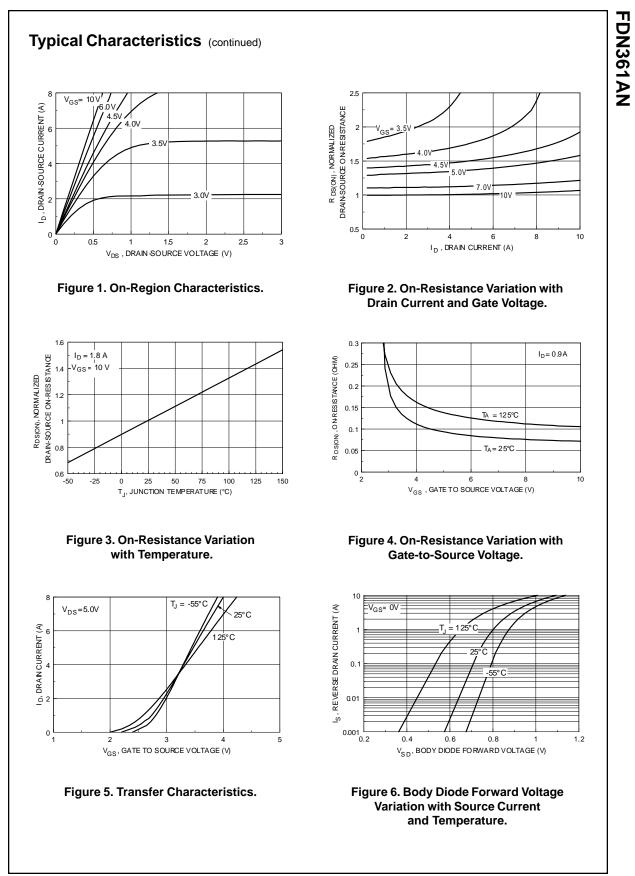


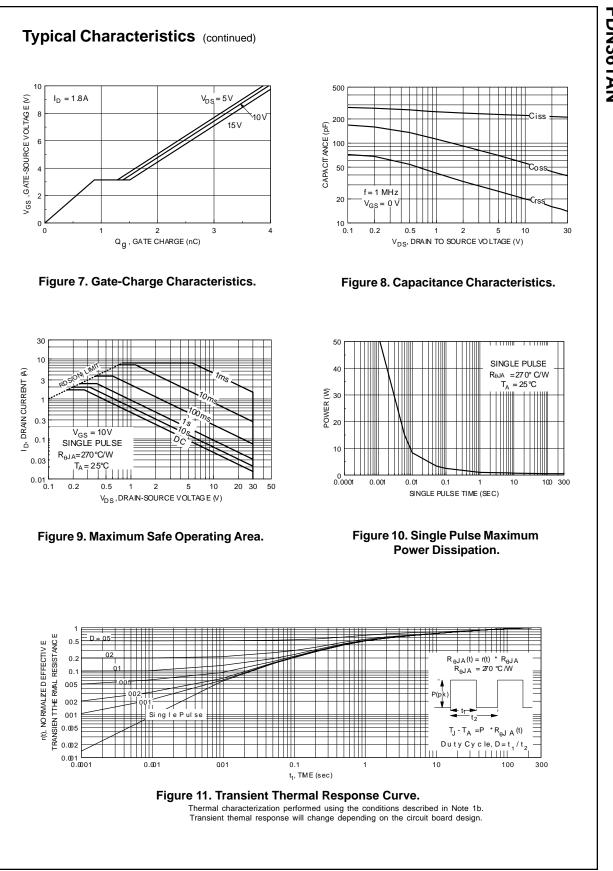
a) 250 °C/W when mounted on a 0.02 in² pad of 2 oz. Cu.

b) 270 °C/W when mounted on a mininum pad.

Scale 1 : 1 on letter size paper

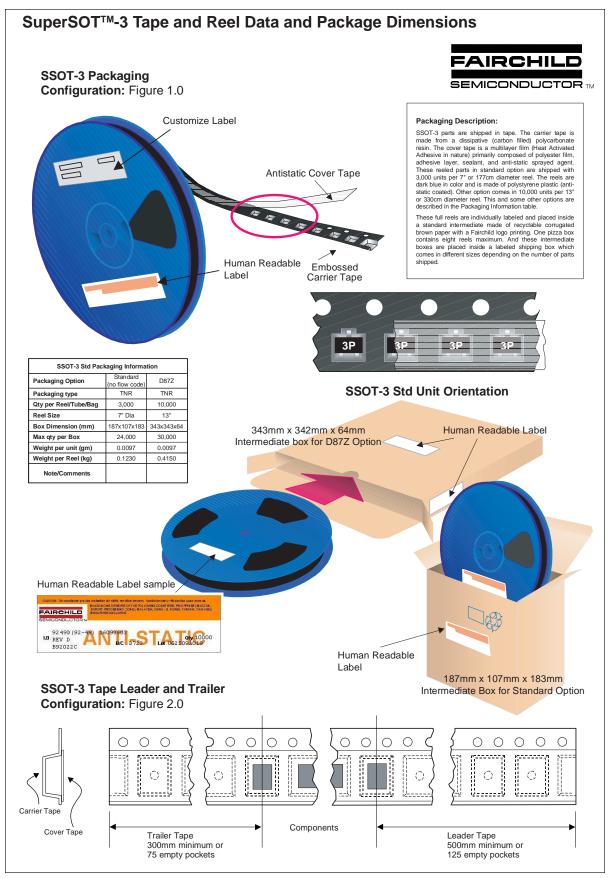
2. Pulse Test: Pulse Width \pm 300 ms, Duty Cycle \pm 2.0%



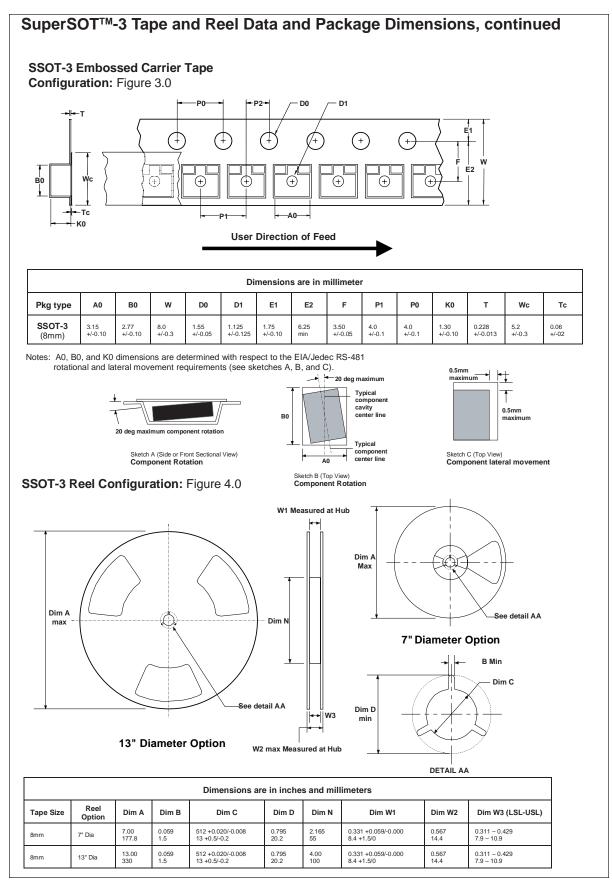


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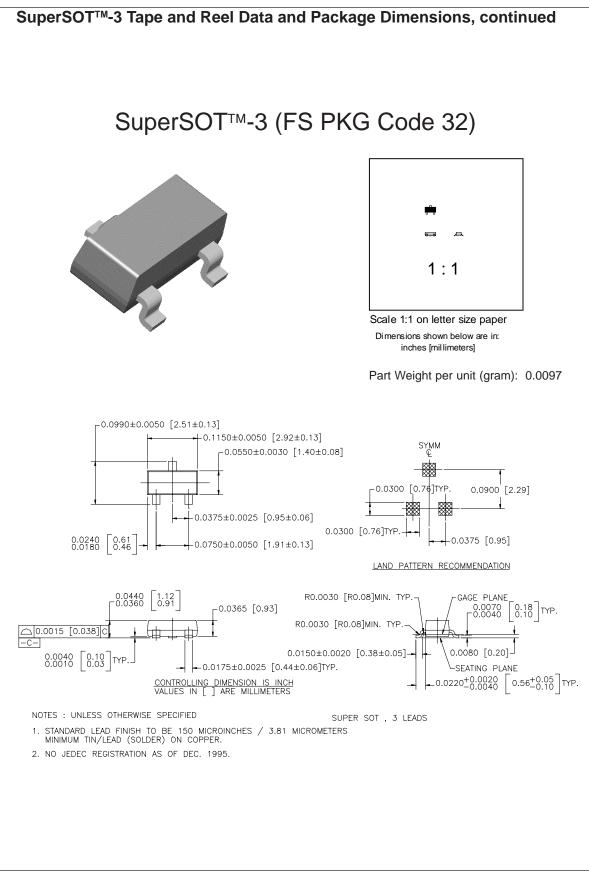
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August 1999, Rev. C



July 1999, Rev. C



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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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